Features

- Ultra small package: 1.0x0.6x0.5mm
- Ultra low capacitance: 0.26pF typical
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
  - – IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±20kV
    - Contact discharge: ±15kV
  - – IEC61000-4-4 (EFT) 40A (5/50ns)
  - – IEC61000-4-5 (Lightning) 4A (8/20μs)
- RoHS Compliant

Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Lead Finish: NiPdAu
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram

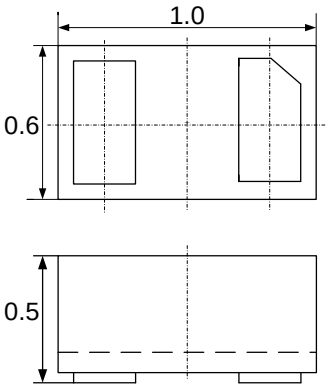
Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- RFID
- FM Antennas
- Peripherals
- Battery, Power Lines

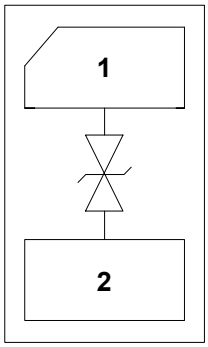
Description

The ESD1210X4 is a 12V bi-directional low capacitance TVS diode, utilizing leading monolithic silicon technology to provide fast response time, very low capacitance and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line.The ESD1210X4 complies with the IEC 61000 -4-2 (ESD) standard with ±15kV air and ±8kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size and high ESD surge protection make ESD1210X4 an ideal choice to protect cell phone, digital cameras, audio players, and many other portable applications.

Dimensions and Pin Configuration



Package Dimensions



Circuit and Pin Schematic

Part Number Code

E	S	D	0	5	1	1	L	1
1	2	3	4	5	6	7	8	9

Product Type	
ESD	TSK Electrostatic suppressor ESD Type

Reverse Working Voltage（V）	
3V3	3.3V
05	5V
16	16V

Line	
1	1-Line
2	2-Line
3	3-Line

directional	
0	Bi
1	Uni

Capacitance Type	
L	Low
X	Normal

Size	
1	0201
2	0402
3	DFN0603
4	DFN1006

★ Code 4 to 9 is optional

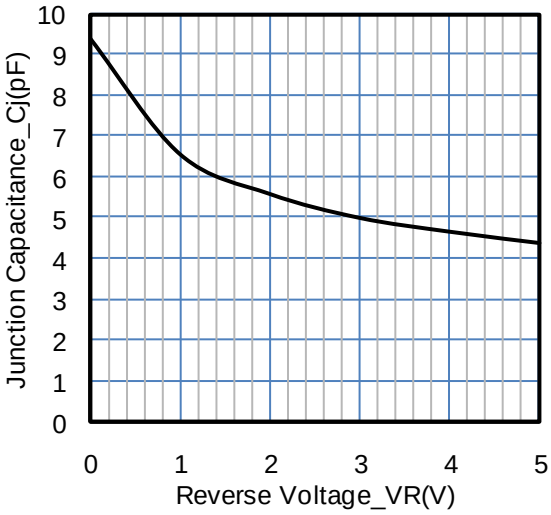
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	100	W
Peak Pulse Current (8/20μs)	Ipp	4	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±18 ±12	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

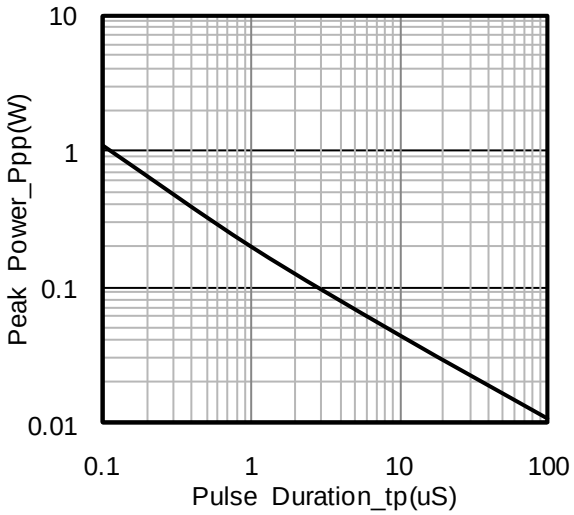
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			12	V	
Breakdown Voltage	V_{BR}	13.3			V	I_T = 1mA
Reverse Leakage Current	I_R			50	nA	V_{RWM} = 12V
Clamping Voltage	V_C			16	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			25	V	I_{PP} = 4A (8 x 20μs pulse)
Junction Capacitance	C_J		10	15	pF	VR = 0V, f = 1MHz

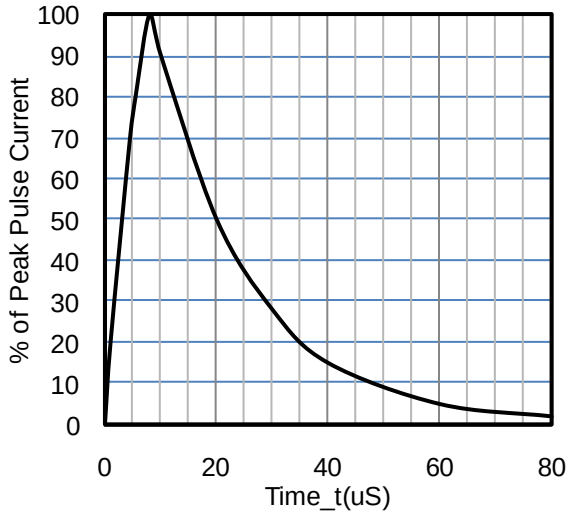
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



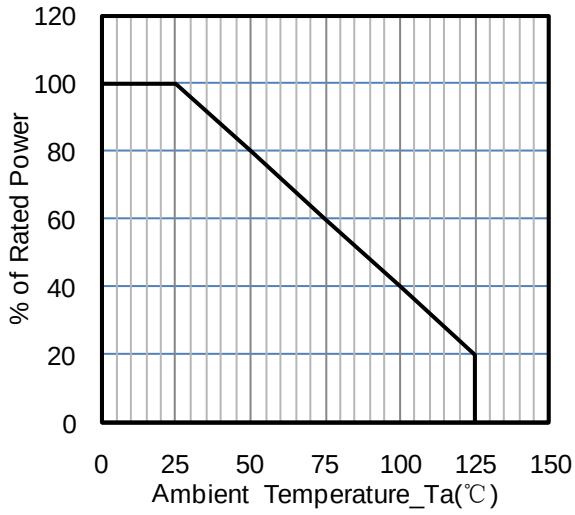
Junction Capacitance vs. Reverse Voltage



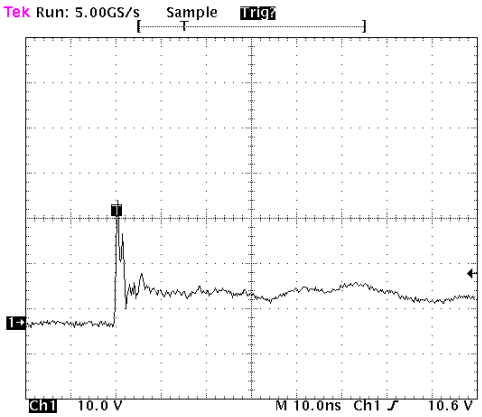
Peak Pulse Power vs. Pulse Time



8 X 20uS Pulse Waveform



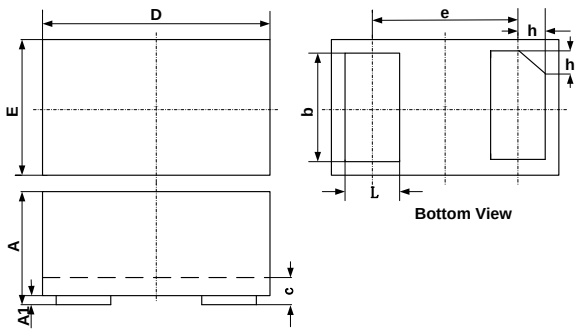
Power Derating Curve



ESD Clamping Voltage

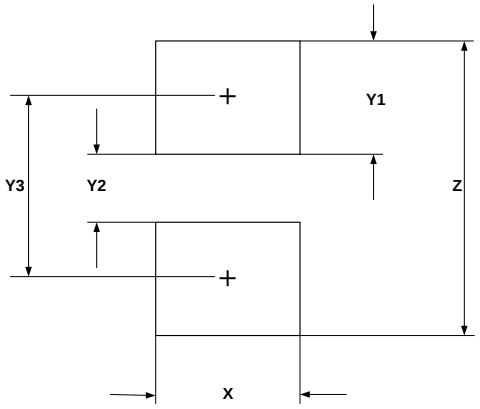
8 kV Contact per IEC61000−4−2

DFN1006-2 Package Outline Drawing



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
h	0.07	0.12	0.17	0.003	0.005	0.007

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052

Ordering Information

Part Number	Packaging	Reel Size
ESD1210X4	10000/Tape & Reel	7 inch